

ABSTRACT OF THE DISCLOSURE

A Group III-V compound semiconductor epitaxial layer has a tilt
5 angle of at most 100 seconds and/or a tilt angle of at most 100 seconds. The
layer is epitaxially grown by use of a mask, wherein the mask satisfies the
equation (1) :

$$h \geq (w/2) \tan \theta \quad \text{----- (1)}$$

where " θ " is a base angle of a facet structure of the Group III-V
10 compound semiconductor layer on the epitaxial growth ; "h" is a thickness
of the mask ; and "w" is an opening width of the mask at its lower level,
and the opening width is defined in a direction included in a plane which is
vertical to both the surface of the base layer and the side face of the facet
structure.